

Title (en)

METHOD FOR PLASMA DICING A SEMI-CONDUCTOR WAFER

Title (de)

VERFAHREN FÜR PLASMA-SCHNEIDEN EINES HALBLEITERWAFERS

Title (fr)

PROCÉDÉ POUR LE DÉCOUPAGE EN DÉS AU PLASMA D'UNE PLAQUETTE SEMI-CONDUCTRICE

Publication

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Application

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Abstract (en)

[origin: US2013230973A1] The present invention provides a method for plasma dicing a substrate, the method comprising providing a process chamber having a wall; providing a plasma source adjacent to the wall of the process chamber; providing a work piece support within the process chamber; placing a work piece onto the work piece support, said work piece having a support film, a frame and the substrate; loading the work piece onto the work piece support; applying a tensional force to the support film; clamping the work piece to the work piece support; generating a plasma using the plasma source; and etching the work piece using the generated plasma.

IPC 8 full level

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